

# Xiangru Kong

## List of Publications by Year in descending order

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20  
papers

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citations

687363

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752698

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20  
docs citations

20  
times ranked

687  
citing authors

#	ARTICLE	IF	CITATIONS
1	Low Energy Implantation into Transition-Metal Dichalcogenide Monolayers to Form Janus Structures. ACS Nano, 2020, 14, 3896-3906.	14.6	136
2	New nanoporous graphyne monolayer as nodal line semimetal: Double Dirac points with an ultrahigh Fermi velocity. Carbon, 2019, 141, 712-718.	10.3	42
3	Carbon-rich carbon nitride monolayers with Dirac cones: Dumbbell C <sub>4</sub> N. Carbon, 2017, 118, 285-290.	10.3	40
4	Quantum anomalous Hall effect in a stable 1T-YN <sub>2</sub> monolayer with a large nontrivial bandgap and a high Chern number. Nanoscale, 2018, 10, 8153-8161.	5.6	35
5	Polytypism in few-layer gallium selenide. Nanoscale, 2020, 12, 8563-8573.	5.6	26
6	Spin transport properties in lower n-acene-graphene nanojunctions. Physical Chemistry Chemical Physics, 2015, 17, 11292-11300.	2.8	22
7	Spin negative differential resistance and high spin filtering behavior realized by devices based on graphene nanoribbons and graphitic carbon nitrides. Organic Electronics, 2014, 15, 3674-3680.	2.6	20
8	Gallium bismuth halide GaBi-X <sub>2</sub> (X = I, Br, Cl) monolayers with distorted hexagonal framework: Novel room-temperature quantum spin Hall insulators. Nano Research, 2017, 10, 2168-2180.	10.4	18
9	The magnetic, electronic, and light-induced topological properties in two-dimensional hexagonal FeX <sub>2</sub> (X = Cl, Br, I) monolayers. Applied Physics Letters, 2020, 116, .	3.3	18
10	Monolayer 1T-LaN <sub>2</sub> : Dirac spin-gapless semiconductor of <i>p</i> -state and Chern insulator with a high Chern number. Applied Physics Letters, 2020, 117, .	3.3	17
11	Thickness and Spin Dependence of Raman Modes in Magnetic Layered Fe <sub>3</sub> GeTe <sub>2</sub> . Advanced Electronic Materials, 2021, 7, 2001159.	5.1	16
12	New group-V elemental bilayers: A tunable structure model with four-, six-, and eight-atom rings. Physical Review B, 2017, 96, .	3.2	15
13	T <sub>4</sub> C <sub>4</sub> graphyne: A 2D carbon allotrope with an intrinsic direct bandgap. Solid State Communications, 2019, 293, 23-27.	1.9	15
14	Topological Dirac semimetal phase in Ge <sub>x</sub> Sn <sub>y</sub> alloys. Applied Physics Letters, 2018, 112, .	3.3	10
15	Ferromagnetism with in-plane magnetization, Dirac spin-gapless semiconducting properties, and tunable topological states in two-dimensional rare-earth metal dinitrides. Physical Review B, 2022, 105, .	3.2	9
16	Electronic transport properties of a dithienylethene-based polymer with different metallic contacts. RSC Advances, 2014, 4, 40941-40950.	3.6	6
17	Rectifying behaviors of an Au/(C <sub>20</sub> ) <sub>2</sub> /Au molecular device induced by the different positions of gate voltage. RSC Advances, 2012, 2, 11349.	3.6	5
18	Role of edge dehydrogenation in magnetization and spin transport of zigzag graphene nanoribbons with line defects. Organic Electronics, 2015, 27, 212-220.	2.6	5

#	ARTICLE	IF	CITATIONS
19	Graphene-based heterostructures with moiré superlattice that preserve the Dirac cone: a first-principles study. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 255302.	1.8	4
20	Floquet band engineering and topological phase transitions in 1T' transition metal dichalcogenides. <i>2D Materials</i> , 2022, 9, 025005.	4.4	4